

Occupancy disorder and magnetism in tetradymite based topological insulators

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Magnetic topological insulators (MTIs) are a hot topic of materials science, promising future availability of spintronics with low energy consumption, quantum computing and phenomena like the Quantized Anomalous Hall Effect (QAHE) [1-2]. MTIs are chemically and structurally akin to the original non-magnetic topological insulators. Of those, the tetradymites Bi_2Te_3 and Sb_2Te_3 have recently proven to allow the introduction of a third magnetic element resulting in magnetically active, topologically non-trivial compounds. A magnetic element can be incorporated either via substitution on the Bi/Sb position in $(\text{Bi}, \text{Sb})_2\text{Te}_3$, or by adding a third element which introduces a new crystallographic site, resulting for example in MnBi_2Te_4 . $(\text{Bi}, \text{Sb})_2\text{Te}_3$ itself and all members of its family exhibit the rhombohedral $R\bar{3}m1$ space group (No. 166) [2]. Therein interchanging sheets of Mn, (Bi, Sb) and Te build septuple layers with the central sheet being Mn (Wyckoff position 3a). Situated between the respective layers is a van der Waals gap (Fig. 1).

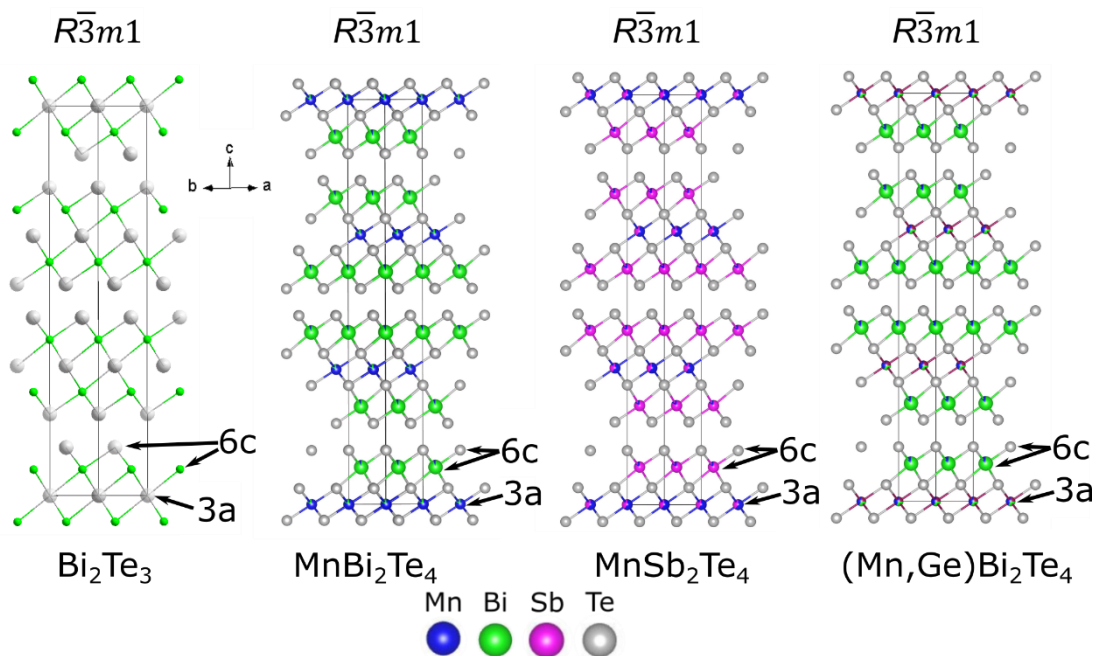


Figure 1: The structure of Bi_2Te_3 [3], MnBi_2Te_4 , MnSb_2Te_4 and $(\text{Mn}, \text{Ge})\text{Bi}_2\text{Te}_4$. All of those compounds are classified as topological insulators and are currently being investigated by us.

Our group was the first to successfully grow single crystals and conduct an in depth study of the physical properties of MnBi_2Te_4 [4-5]. Single crystal diffraction experiments reported in that study showed intermixing of Mn and Bi and since then several studies have reported intermixing of the two elements ($\text{MnBi}_{2.14}\text{Te}_{3.96}$ [6], $\text{Mn}_{1.01}\text{Bi}_{1.99}\text{Te}_4$ and $\text{Mn}_{0.98}\text{Bi}_{2.05}\text{Te}_4$ [7]). While a lot of attention has been given to MnBi_2Te_4 , MnSb_2Te_4 proved to be synthetically achievable too. Similar to MnBi_2Te_4 , MnSb_2Te_4 features intermixing of Mn and Sb ($\text{Mn}_{0.852}\text{Sb}_{2.296}\text{Te}_4$ [8]). For MnSb_2Te_4 , a recent study by Murakami et al. uncovers the impact of finding a certain amount of the magnetic Mn on the position of the non-magnetic Sb [9]. According to their discoveries, this changes the magnetic order from antiferromagnetic to ferrimagnetic.

These compounds are known to react sensitively to synthesis procedure and tempering history. Hence, our studies aim at understanding the greater connection between synthesis aspects and the resulting structural and physical properties. More precisely we

studied MnBi_2Te_4 and MnSb_2Te_4 containing various amounts of Mn and other analogues of these systems. In these studies we uncovered, that the magnetism in MnSb_2Te_4 is even more sensitive to annealing procedures than previously expected.

- [1] Y. Ando, Journal of the Physical Society of Japan, (2013), 82, 102001
- [2] I. I. Klimovskikh, M. M. Otrokov, D. Estyunin, et al., Quantum Materials, (2020), 54.
- [3] Y. Feutelais, B. Legendre, N. Rodier, V. Agafonov, Materials Research Bulletin, (1993), 28, 591-596
- [4] A. Zeugner, F. Nietschke, A. U. B. Wolter, et al., Chemistry of Materials, (2019), 31, 2795-2806.
- [5] M. M. Otrokov, I. I. Klimovskikh, H. Bentmann, et al., Nature, (2019), 576, 416-422.
- [6] H. Li, S. Liu, C. Liu, et al., Physical Chemistry Chemical Physics, (2020), 22, 556-563.
- [7] M.-H. Du, J. Yan, V. R. Cooper, M. Eisenbach, Advanced Functional Materials, (2020), 2006516.
- [8] L. Zhou, Z. Tan, D. Yan, et al., Physical Review B, (2020), 102, 85114.
- [9] T. Murakami, Y. Nambu, T. Koretsune, et al., Physical Review B, (2019), 100, 195103.

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